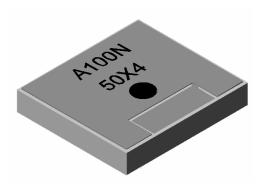




Chip Termination 100 Watts, 50Ω



Features:

- RoHS Compliant
- 100 Watts
- DC 2.7 GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested
- Small Size

Description

The A100N50X4 is high performance Aluminum Nitride (AIN) chip termination intended as an alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications

Resistive Element Thick film
Substrate AIN Ceramic

Terminal Finish Matte Tin over Nickel Barrier

Operating Temperature -55 to +150°C (See de rating chart)

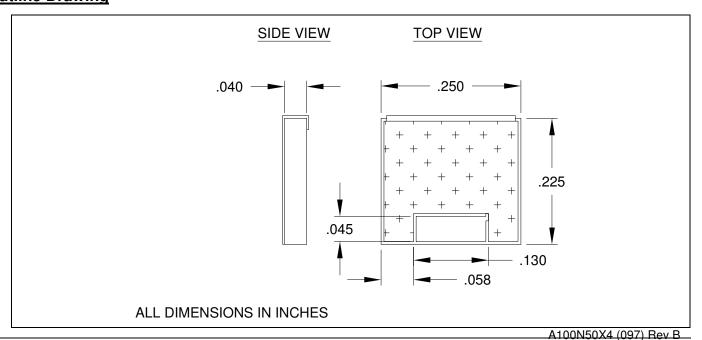
Tolerance is ±0.010", unless otherwise specified. Designed to meet of exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications

Resistance Value:50 Ohms, $\pm 2\%$ Power:100 WattsFrequency Range:DC -2.7 GHzV.S.W.R.1.1:1 to 2.7 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

Outline Drawing





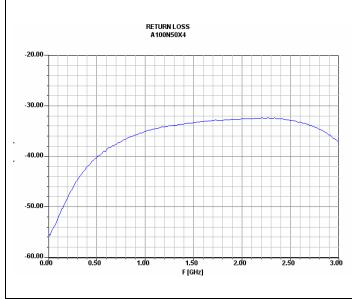
Available on Tape and Reel For Pick and Place Manufacturing. USA/Canada: (315) 432-8909 Toll Free: (800) 544-2414 Europe: +44 2392-232392

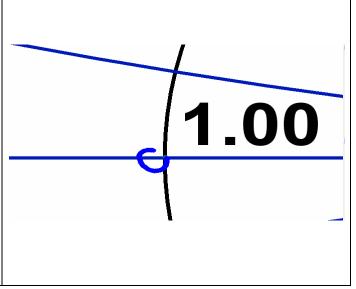




Typical Performance:

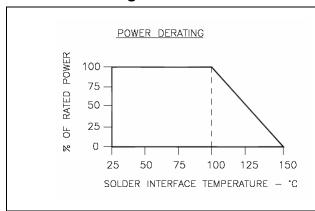


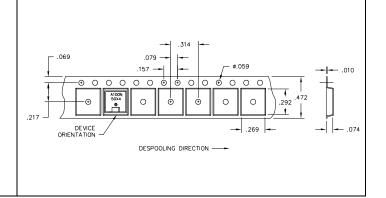




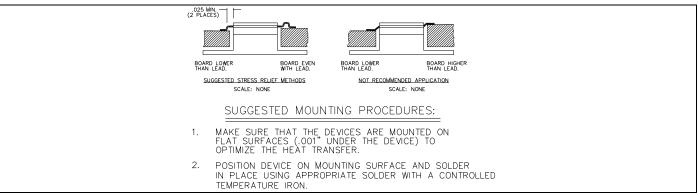
Power De-rating:

Tape & Reel:





Mounting Footprint and Procedure:



A100N50X4 (097) Rev B

USA/Canada: Toll Free: Europe: (315) 432-8909 (800) 544-2414 +44 2392-232392

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